



WILLAS 

active 

BSS123LT1

N-CHANNEL POWER MOSFET

FEATURE

- Pb-Free package is available

RoHS product for packing code suffix "G"

Halogen free product for packing code suffix "H"

DEVICE MARKING AND ORDERING INFORMATION

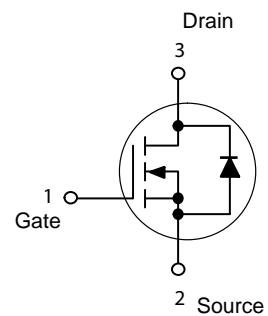
Device	Marking	Shipping
BSS123LT1	SA	3000/Tape&Reel



SOT-23

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	100	Vdc
Gate-Source Voltage – Continuous – Non-repetitive ($t_p \leq 50 \mu s$)	V_{GS} V_{GSM}	± 20 ± 40	Vdc Vpk
Drain Current Continuous (Note 1.) Pulsed (Note 2.)	I_D I_{DM}	0.17 0.68	Adc



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 3.) $T_A = 25^\circ C$ Derate above $25^\circ C$	P_D	225 1.8	mW mW/ $^\circ C$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ C/W$
Junction and Storage Temperature	T_J, T_{Stg}	-55 to +150	$^\circ C$

1. The Power Dissipation of the package may result in a lower continuous drain current.
2. Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$.
3. FR-5 = $1.0 \times 0.75 \times 0.062$ in.



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BSS123LT1**ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)**

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 250 \mu\text{Adc}$)	$V_{(\text{BR})DSS}$	100	-	-	Vdc
Zero Gate Voltage Drain Current ($V_{GS} = 0$, $V_{DS} = 100 \text{ Vdc}$) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	I_{DSS}	-	-	15 60	μAdc
Gate-Body Leakage Current ($V_{GS} = 20 \text{ Vdc}$, $V_{DS} = 0$)	I_{GSS}	-	-	50	nAdc

ON CHARACTERISTICS (Note 4.)

Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 1.0 \text{ mAdc}$)	$V_{GS(\text{th})}$	0.8	-	2.8	Vdc
Static Drain-Source On-Resistance ($V_{GS} = 10 \text{ Vdc}$, $I_D = 100 \text{ mAdc}$)	$r_{DS(\text{on})}$	-	5.0	6.0	Ω
Forward Transconductance ($V_{DS} = 25 \text{ Vdc}$, $I_D = 100 \text{ mAdc}$)	g_{fs}	80	-	-	mmhos

DYNAMIC CHARACTERISTICS

Input Capacitance ($V_{DS} = 25 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)	C_{iss}	-	20	-	pF
Output Capacitance ($V_{DS} = 25 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)	C_{oss}	-	9.0	-	pF
Reverse Transfer Capacitance ($V_{DS} = 25 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)	C_{rss}	-	4.0	-	pF

SWITCHING CHARACTERISTICS(4)

Turn-On Delay Time Turn-Off Delay Time	($V_{CC} = 30 \text{ Vdc}$, $I_C = 0.28 \text{ Adc}$, $V_{GS} = 10 \text{ Vdc}$, $R_{GS} = 50 \Omega$)	$t_{d(on)}$ $t_{d(off)}$	- -	20 40	- -	ns ns
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REVERSE DIODE

Diode Forward On-Voltage ($I_D = 0.34 \text{ Adc}$, $V_{GS} = 0 \text{ Vdc}$)	V_{SD}	-	-	1.3	V
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4. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

N-CHANNEL POWER MOSFET

TYPICAL ELECTRICAL CHARACTERISTICS

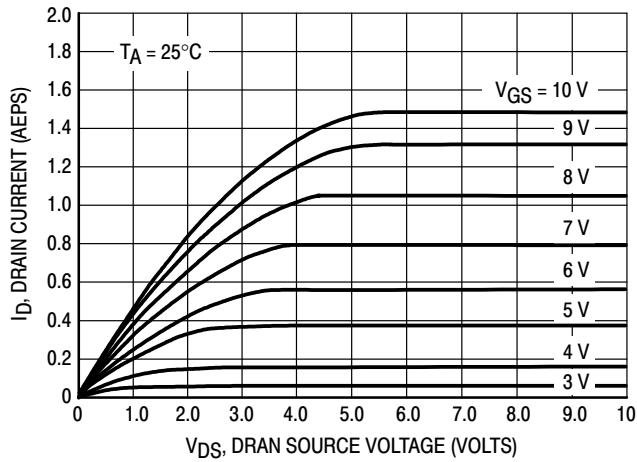


Figure 1. Ohmic Region

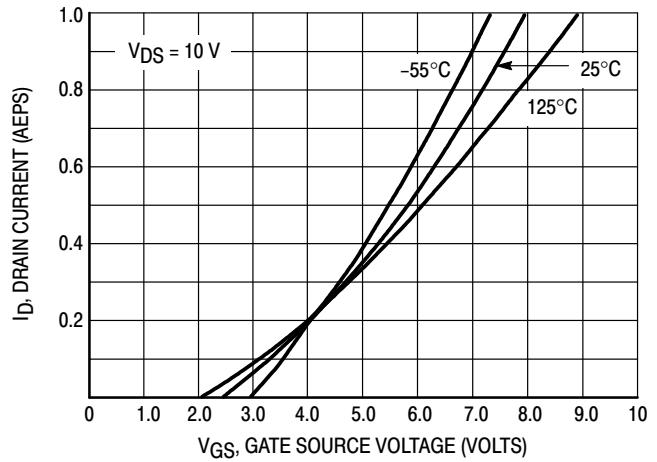


Figure 2. Transfer Characteristics

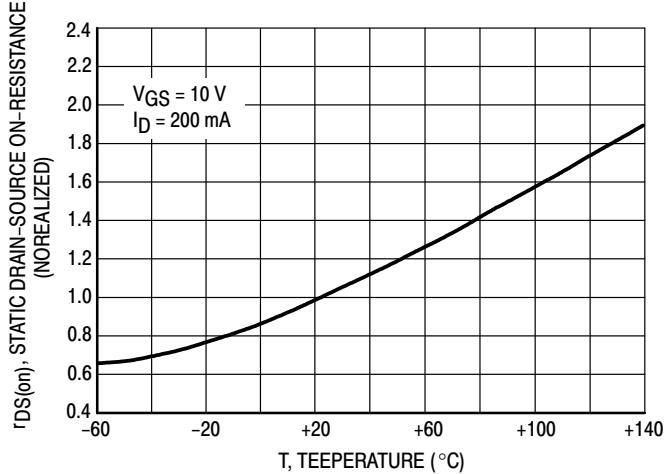


Figure 3. Temperature versus Static Drain-Source On-Resistance

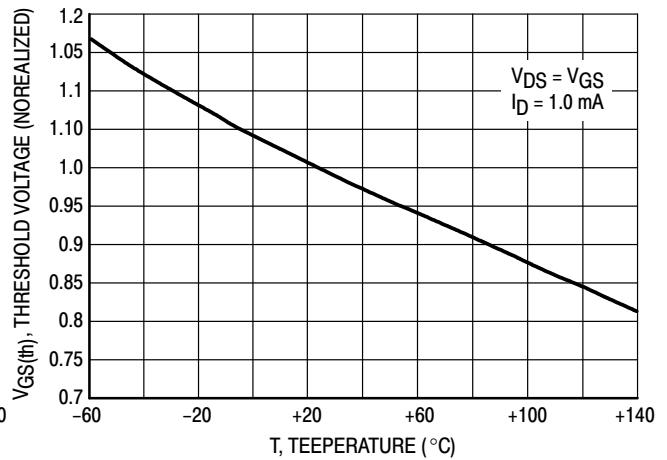
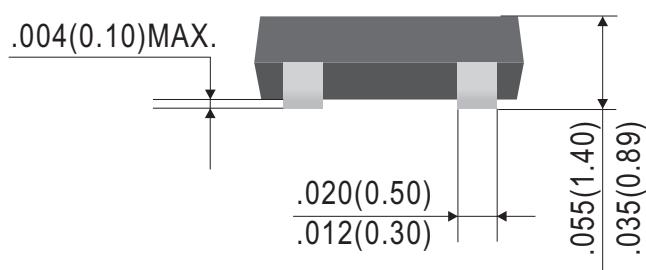
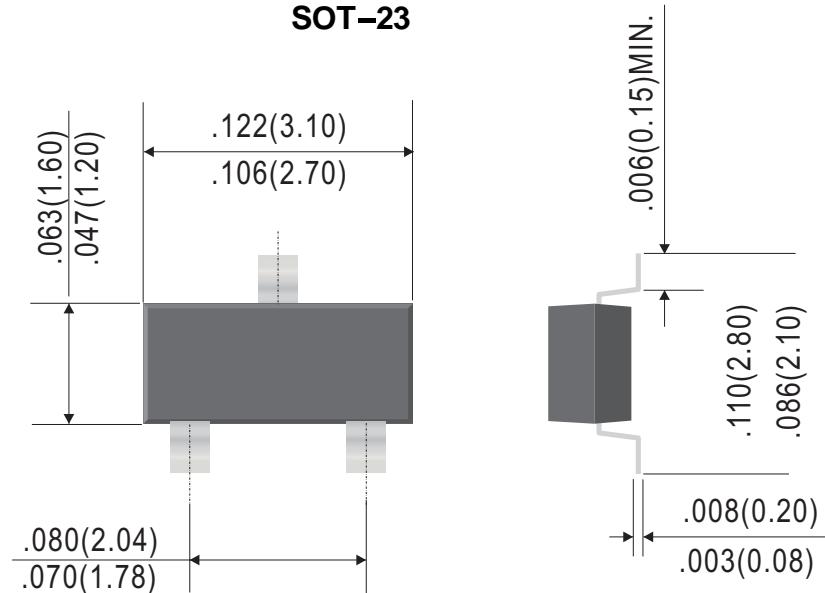
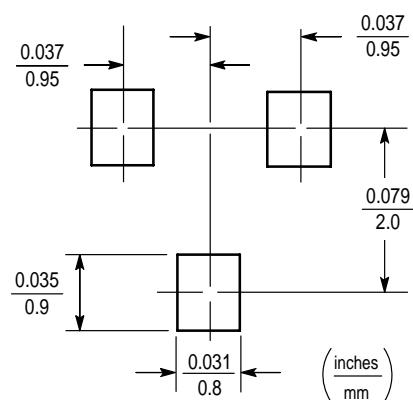


Figure 4. Temperature versus Gate Threshold Voltage

N-CHANNEL POWER MOSFET
SOT-23


Dimensions in inches and (millimeters)





BSS123LT1

N-CHANNEL POWER MOSFET

Ordering Information:

Device PN	Packing
BSS123LT1G ⁽¹⁾ -WS	Tape&Reel: 3 Kpcs/Reel

Note: (1) RoHS product for packing code suffix "G" ; Halogen free product for packing code suffix "H"

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